

# NTMYS011N04C

## Power MOSFET

40 V, 12 mΩ, 35 A, Single N-Channel

### Features

- Small Footprint (5x6 mm) for Compact Design
- Low  $R_{DS(on)}$  to Minimize Conduction Losses
- Low  $Q_G$  and Capacitance to Minimize Driver Losses
- LFPK4 Package, Industry Standard
- These Devices are Pb-Free and are RoHS Compliant

### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

| Parameter                                                                                                |                                                   |                           | Symbol            | Value       | Unit             |
|----------------------------------------------------------------------------------------------------------|---------------------------------------------------|---------------------------|-------------------|-------------|------------------|
| Drain-to-Source Voltage                                                                                  |                                                   |                           | $V_{DS}$          | 40          | V                |
| Gate-to-Source Voltage                                                                                   |                                                   |                           | $V_{GS}$          | $\pm 20$    | V                |
| Continuous Drain Current $R_{\theta JC}$ (Notes 1, 2, 3)                                                 | Steady State                                      | $T_C = 25^\circ\text{C}$  | $I_D$             | 35          | A                |
|                                                                                                          |                                                   | $T_C = 100^\circ\text{C}$ |                   | 20          |                  |
| Power Dissipation $R_{\theta JC}$ (Notes 1, 2)                                                           |                                                   | $T_C = 25^\circ\text{C}$  | $P_D$             | 28          | W                |
|                                                                                                          |                                                   | $T_C = 100^\circ\text{C}$ |                   | 9.1         |                  |
| Continuous Drain Current $R_{\theta JA}$ (Notes 1, 2, 3)                                                 | Steady State                                      | $T_A = 25^\circ\text{C}$  | $I_D$             | 13          | A                |
|                                                                                                          |                                                   | $T_A = 100^\circ\text{C}$ |                   | 9.1         |                  |
| Power Dissipation $R_{\theta JA}$ (Notes 1, 2)                                                           |                                                   | $T_A = 25^\circ\text{C}$  | $P_D$             | 3.8         | W                |
|                                                                                                          |                                                   | $T_A = 100^\circ\text{C}$ |                   | 1.9         |                  |
| Pulsed Drain Current                                                                                     | $T_A = 25^\circ\text{C}$ , $t_p = 10 \mu\text{s}$ |                           | $I_{DM}$          | 173         | A                |
| Operating Junction and Storage Temperature                                                               |                                                   |                           | $T_J$ , $T_{stg}$ | -55 to +175 | $^\circ\text{C}$ |
| Source Current (Body Diode)                                                                              |                                                   |                           | $I_S$             | 24          | A                |
| Single Pulse Drain-to-Source Avalanche Energy ( $T_J = 25^\circ\text{C}$ , $I_{L(pk)} = 1.9 \text{ A}$ ) |                                                   |                           | $E_{AS}$          | 75          | mJ               |
| Lead Temperature for Soldering Purposes (1/8" from case for 10 s)                                        |                                                   |                           | $T_L$             | 260         | $^\circ\text{C}$ |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

### THERMAL RESISTANCE MAXIMUM RATINGS

| Parameter                                   | Symbol          | Value | Unit               |
|---------------------------------------------|-----------------|-------|--------------------|
| Junction-to-Case – Steady State             | $R_{\theta JC}$ | 5.3   | $^\circ\text{C/W}$ |
| Junction-to-Ambient – Steady State (Note 2) | $R_{\theta JA}$ | 39    |                    |

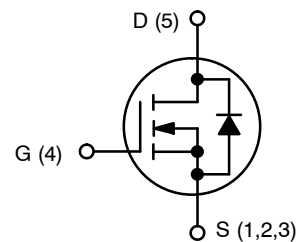
1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Surface-mounted on FR4 board using a 650 mm<sup>2</sup>, 2 oz. Cu pad.
3. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.



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| $V_{(BR)DSS}$ | $R_{DS(ON)} \text{ MAX}$ | $I_D \text{ MAX}$ |
|---------------|--------------------------|-------------------|
| 40 V          | 12 mΩ @ 10 V             | 35 A              |

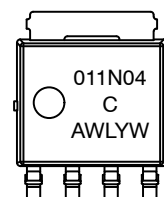


N-CHANNEL MOSFET



LFPK4  
CASE 760AB

### MARKING DIAGRAM



011N04C = Specific Device Code  
A = Assembly Location  
WL = Wafer Lot  
Y = Year  
W = Work Week

### ORDERING INFORMATION

See detailed ordering, marking and shipping information on page 5 of this data sheet.

# NTMYS011N04C

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise specified)

| Parameter | Symbol | Test Condition | Min | Typ | Max | Unit |
|-----------|--------|----------------|-----|-----|-----|------|
|-----------|--------|----------------|-----|-----|-----|------|

### OFF CHARACTERISTICS

|                                                           |                   |                                                     |                           |    |     |                      |
|-----------------------------------------------------------|-------------------|-----------------------------------------------------|---------------------------|----|-----|----------------------|
| Drain-to-Source Breakdown Voltage                         | $V_{(BR)DSS}$     | $V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$ | 40                        |    |     | V                    |
| Drain-to-Source Breakdown Voltage Temperature Coefficient | $V_{(BR)DSS}/T_J$ |                                                     |                           | 25 |     | mV/ $^\circ\text{C}$ |
| Zero Gate Voltage Drain Current                           | $I_{DSS}$         | $V_{GS} = 0\text{ V}, V_{DS} = 40\text{ V}$         | $T_J = 25^\circ\text{C}$  |    | 10  | $\mu\text{A}$        |
|                                                           |                   |                                                     | $T_J = 125^\circ\text{C}$ |    | 250 |                      |
| Gate-to-Source Leakage Current                            | $I_{GSS}$         | $V_{DS} = 0\text{ V}, V_{GS} = 20\text{ V}$         |                           |    | 100 | nA                   |

### ON CHARACTERISTICS (Note 4)

|                                            |                  |                                                |     |      |     |                      |
|--------------------------------------------|------------------|------------------------------------------------|-----|------|-----|----------------------|
| Gate Threshold Voltage                     | $V_{GS(TH)}$     | $V_{GS} = V_{DS}, I_D = 20\text{ }\mu\text{A}$ | 2.5 |      | 3.5 | V                    |
| Negative Threshold Temperature Coefficient | $V_{GS(TH)}/T_J$ |                                                |     | -7.6 |     | mV/ $^\circ\text{C}$ |
| Drain-to-Source On Resistance              | $R_{DS(on)}$     | $V_{GS} = 10\text{ V}, I_D = 10\text{ A}$      |     | 10   | 12  | m $\Omega$           |
| Forward Transconductance                   | $g_{FS}$         | $V_{DS} = 15\text{ V}, I_D = 10\text{ A}$      |     | 111  |     | S                    |

### CHARGES, CAPACITANCES & GATE RESISTANCE

|                              |              |                                                                 |  |     |  |    |
|------------------------------|--------------|-----------------------------------------------------------------|--|-----|--|----|
| Input Capacitance            | $C_{ISS}$    | $V_{GS} = 0\text{ V}, f = 1\text{ MHz}, V_{DS} = 25\text{ V}$   |  | 420 |  | pF |
| Output Capacitance           | $C_{OSS}$    |                                                                 |  | 230 |  |    |
| Reverse Transfer Capacitance | $C_{RSS}$    |                                                                 |  | 11  |  |    |
| Total Gate Charge            | $Q_{G(TOT)}$ | $V_{GS} = 10\text{ V}, V_{DS} = 32\text{ V}, I_D = 10\text{ A}$ |  | 7.9 |  | nC |
| Threshold Gate Charge        | $Q_{G(TH)}$  |                                                                 |  | 1.6 |  |    |
| Gate-to-Source Charge        | $Q_{GS}$     |                                                                 |  | 2.5 |  |    |
| Gate-to-Drain Charge         | $Q_{GD}$     |                                                                 |  | 1.5 |  |    |
| Plateau Voltage              | $V_{GP}$     |                                                                 |  | 4.7 |  | V  |

### SWITCHING CHARACTERISTICS (Note 5)

|                     |              |                                                                                        |  |     |  |    |
|---------------------|--------------|----------------------------------------------------------------------------------------|--|-----|--|----|
| Turn-On Delay Time  | $t_{d(ON)}$  | $V_{GS} = 10\text{ V}, V_{DS} = 32\text{ V}, I_D = 10\text{ A}, R_G = 1\text{ }\Omega$ |  | 8.0 |  | ns |
| Rise Time           | $t_r$        |                                                                                        |  | 16  |  |    |
| Turn-Off Delay Time | $t_{d(OFF)}$ |                                                                                        |  | 16  |  |    |
| Fall Time           | $t_f$        |                                                                                        |  | 5.0 |  |    |

### DRAIN-SOURCE DIODE CHARACTERISTICS

|                         |          |                                                                              |                           |     |      |     |   |
|-------------------------|----------|------------------------------------------------------------------------------|---------------------------|-----|------|-----|---|
| Forward Diode Voltage   | $V_{SD}$ | $V_{GS} = 0\text{ V}, I_S = 10\text{ A}$                                     | $T_J = 25^\circ\text{C}$  |     | 0.84 | 1.2 | V |
|                         |          |                                                                              | $T_J = 125^\circ\text{C}$ |     | 0.71 |     |   |
| Reverse Recovery Time   | $t_{RR}$ | $V_{GS} = 0\text{ V}, dI_S/dt = 100\text{ A}/\mu\text{s}, I_S = 10\text{ A}$ |                           | 19  |      | ns  |   |
| Charge Time             | $t_a$    |                                                                              |                           | 9.0 |      |     |   |
| Discharge Time          | $t_b$    |                                                                              |                           | 10  |      |     |   |
| Reverse Recovery Charge | $Q_{RR}$ |                                                                              |                           | 6.7 |      | nC  |   |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulse Test: pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .

5. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

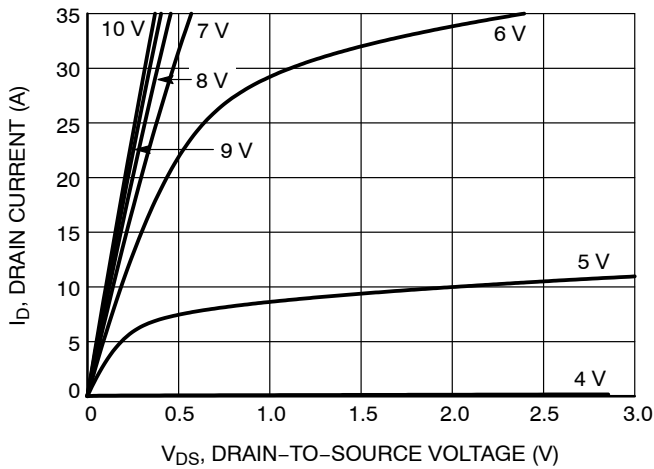


Figure 1. On-Region Characteristics

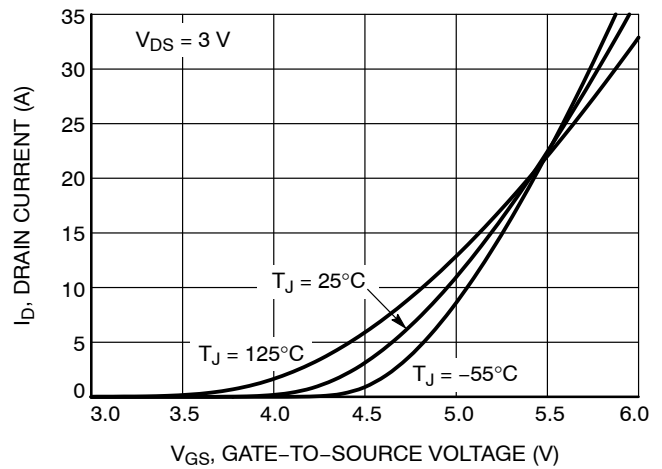


Figure 2. Transfer Characteristics

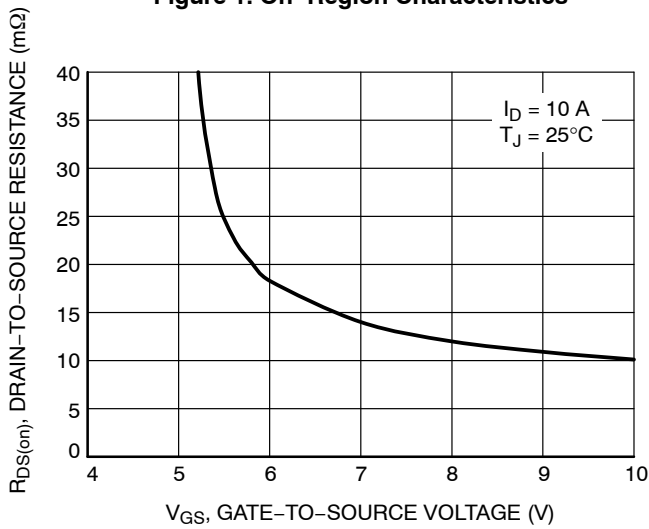


Figure 3. On-Resistance vs. Gate-to-Source Voltage

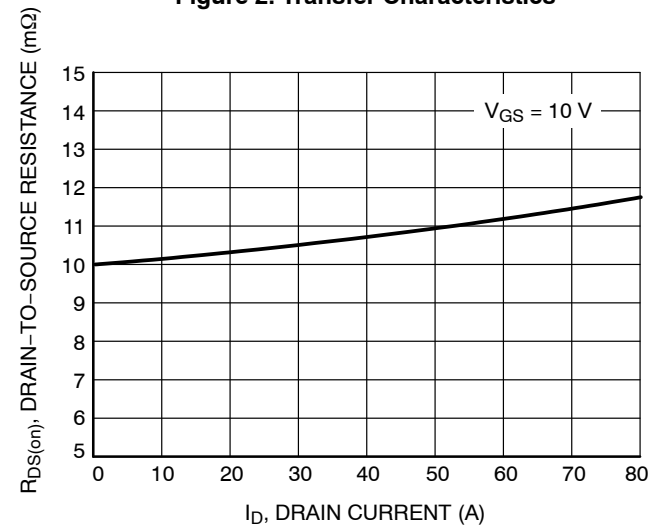


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

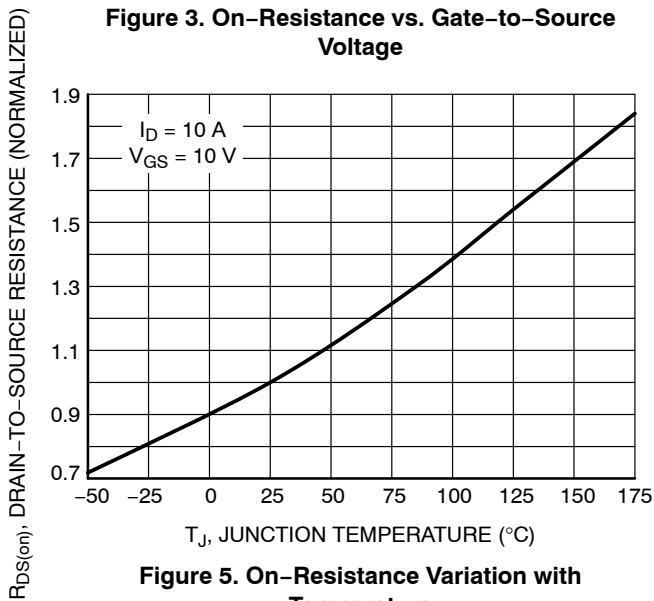


Figure 5. On-Resistance Variation with Temperature

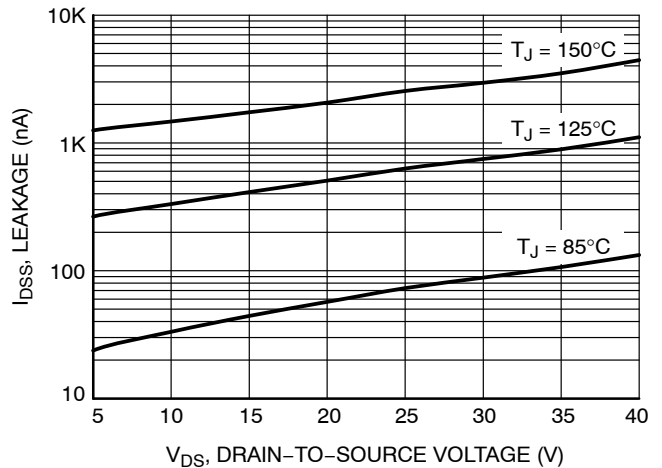


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

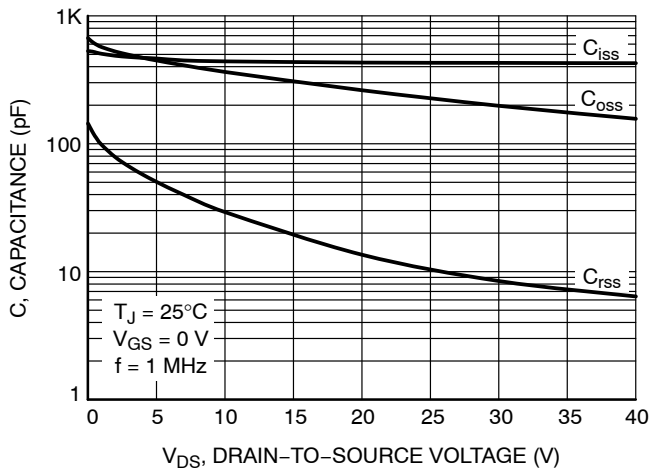


Figure 7. Capacitance Variation

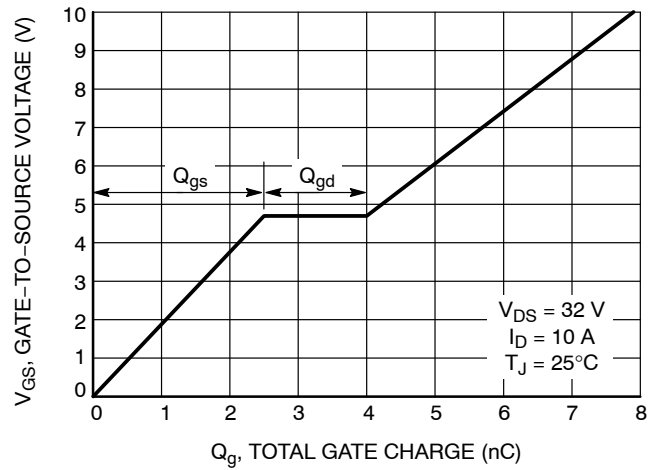


Figure 8. Gate-to-Source Voltage vs. Total Charge

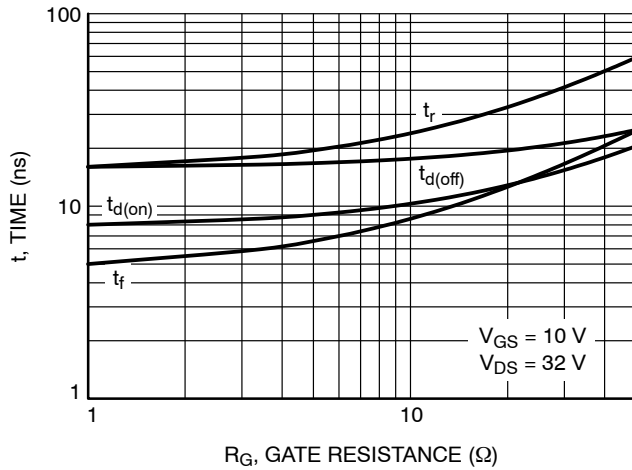


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

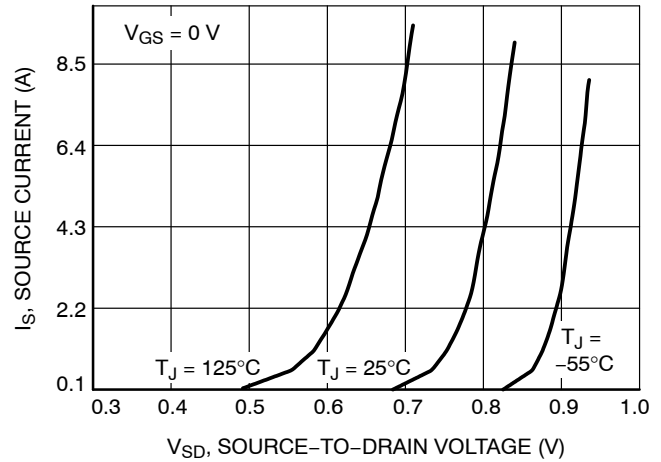


Figure 10. Diode Forward Voltage vs. Current

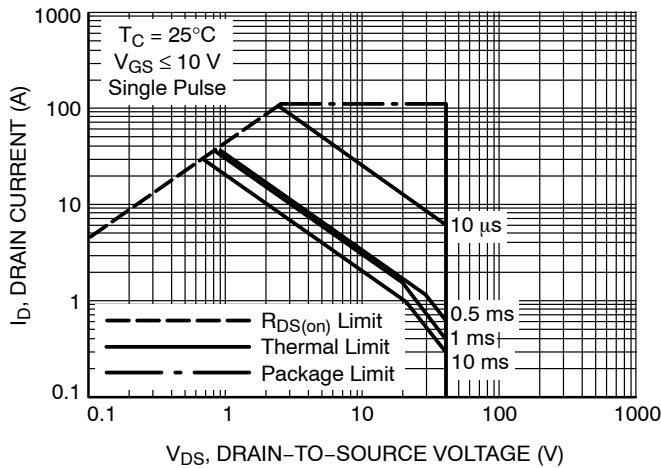


Figure 11. Maximum Rated Forward Biased Safe Operating Area

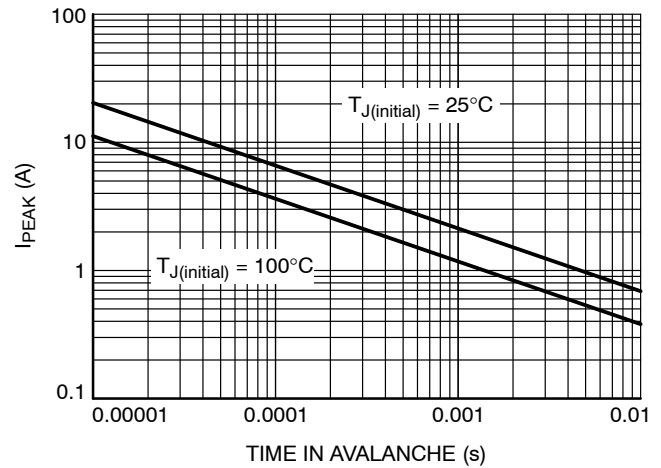


Figure 12. Maximum Drain Current vs. Time in Avalanche

# NTMYS011N04C

## TYPICAL CHARACTERISTICS

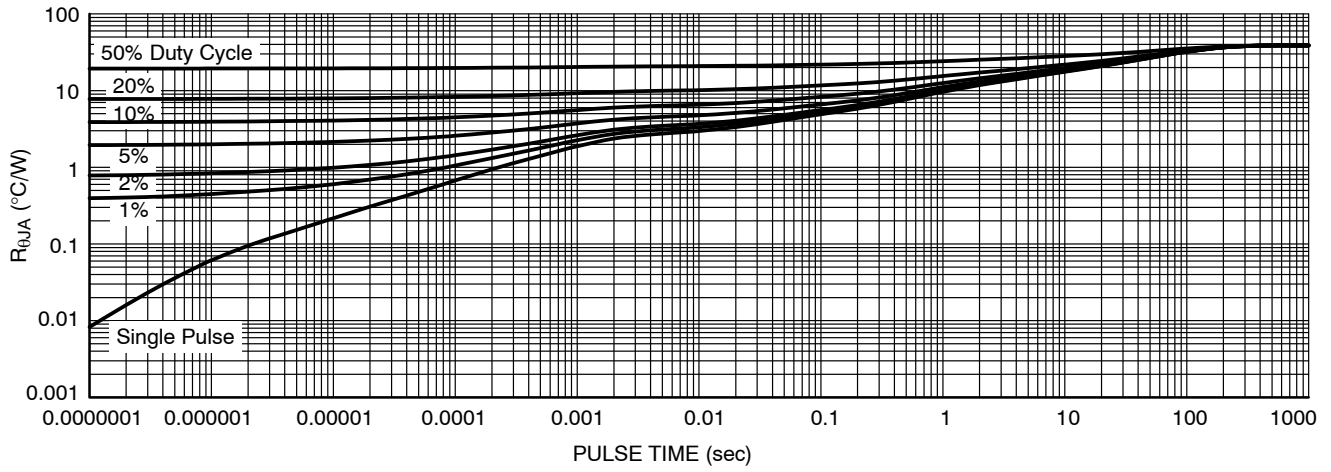


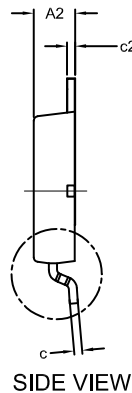
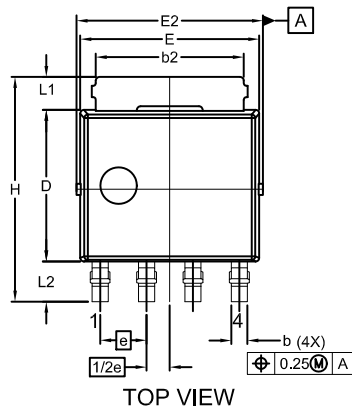
Figure 13. Thermal Characteristics

### DEVICE ORDERING INFORMATION

| Device          | Marking | Package             | Shipping <sup>†</sup> |
|-----------------|---------|---------------------|-----------------------|
| NTMYS011N04CTWG | 011N04C | LFPAK4<br>(Pb-Free) | 3000 / Tape & Reel    |

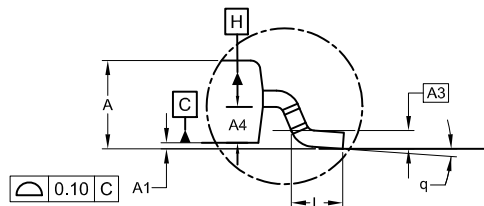
<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

## PACKAGE DIMENSIONS

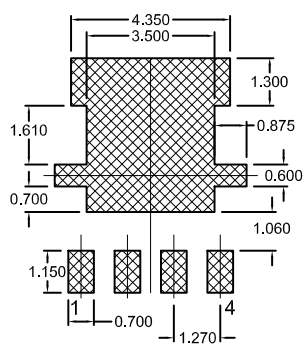
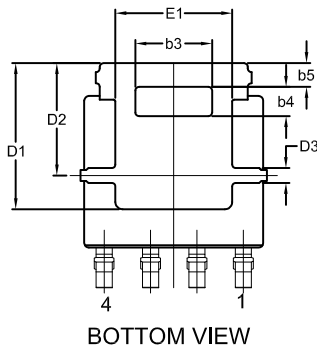
LFPAK4 5x6  
CASE 760AB  
ISSUE B

## NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.150mm PER SIDE.
4. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
5. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.



SCALE: 2:1



| UNIT IN MILLIMETER |      |          |      |
|--------------------|------|----------|------|
| DIM                | MIN  | NOM      | MAX  |
| A                  | 1.10 | 1.20     | 1.30 |
| A1                 | 0.00 | 0.08     | 0.15 |
| A2                 | 1.10 | 1.15     | 1.20 |
| A3                 |      | 0.25     |      |
| A4                 | 0.45 | 0.50     | 0.55 |
| b                  | 0.40 | 0.45     | 0.50 |
| b2                 | 3.80 | 4.10     | 4.40 |
| b3                 | 2.00 | 2.10     | 2.20 |
| b4                 | 0.70 | 0.80     | 0.90 |
| b5                 | 0.55 | 0.65     | 0.75 |
| c                  | 0.19 | 0.22     | 0.25 |
| c2                 | 0.19 | 0.22     | 0.25 |
| D                  | 4.05 | 4.15     | 4.25 |
| D1                 | 3.80 | 4.00     | 4.20 |
| D2                 | 3.00 | 3.10     | 3.20 |
| D3                 | 0.30 | 0.40     | 0.50 |
| E                  | 4.80 | 4.90     | 5.00 |
| E1                 | 3.10 | 3.20     | 3.30 |
| E2                 | 5.00 | 5.15     | 5.30 |
| e                  |      | 1.27 BSC |      |
| H                  | 6.00 | 6.15     | 6.30 |
| L                  | 0.40 | 0.65     | 0.85 |
| L1                 | 0.80 | 0.90     | 1.00 |
| L2                 | 0.80 | 1.05     | 1.30 |
| q                  | 0°   | 4°       | 8°   |

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